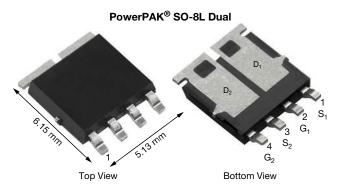
SQJ951EP

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Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET

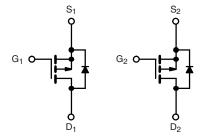


FEATURES

- TrenchFET[®] Power MOSFET
- AEC-Q101 qualified ^d
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



| PRODUCT SUMMARY | |
|---|-------|
| V _{DS} (V) | - 30 |
| $R_{DS(on)} (\Omega)$ at V_{GS} = - 10 V | 0.017 |
| $R_{DS(on)}$ (Ω) at V_{GS} = - 4.5 V | 0.036 |
| I _D (A) | - 30 |
| Configuration | Dual |



P-Channel MOSFET P-Channel MOSFET

| ORDERING INFORMATION | |
|---------------------------------|---|
| Package | PowerPAK SO-8L |
| Lead (Pb)-free and halogen-free | SQJ951EP (for detailed order number please see <u>www.vishay.com/doc?79771</u>) |

| ABSOLUTE MAXIMUM RATINGS (| T _C = 25 °C, unles | s otherwise noted | (k | |
|---|-------------------------------------|---|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Drain-source voltage | | V _{DS} | - 30 | v |
| Gate-source voltage | | V _{GS} | ± 20 | v |
| Continuous drain current | T _C = 25 °C ^a | 1 | - 30 | |
| Continuous drain current | T _C = 125 °C | I _D | - 28 | |
| Continuous source current (diode conduction) ^a | | I _S | - 30 | A |
| Pulsed drain current ^b | | I _{DM} | - 120 | |
| Single pulse avalanche current | L = 0.1 mH | I _{AS} | - 27 | |
| Single pulse avalanche energy | L = 0.1 MH | E _{AS} | 36.5 | mJ |
| Maximum power dissipation ^b | T _C = 25 °C | PD | 56 | w |
| Maximum power dissipation - | T _C = 125 °C | Γ _C = 125 °C Γ ^D 18.5 | | |
| Operating junction and storage temperature range | T _J , T _{stg} | - 55 to + 175 | °C | |
| Soldering recommendations (peak temperature) | e, f | | 260 | |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|------------------------|-------------------|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Junction-to-ambient | PCB mount ^c | R _{thJA} | 85 | °C/W |
| Junction-to-case (drain) | | R _{thJC} | 2.7 | 0/00 |

Notes

- a. Package limited
- b. Pulse test; pulse width $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing
- e. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

S21-0678-Rev. B, 21-Jun-2021

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| PARAMETER | SYMBOL | TES | TEST CONDITIONS | | TYP. | MAX. | UNIT |
|---|--------------------------|---------------------------------------|---|-------|-------|-------|------|
| Static | • | - | | | | | |
| Drain-source breakdown voltage | V _{DS} | V _{GS} | = 0, I _D = - 250 μA | - 30 | - | - | v |
| Gate-source threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = -250 \ \mu A$ | | - 1.5 | - 2.0 | - 2.5 | v |
| Gate-source leakage | I _{GSS} | V _{DS} = | 0 V, $V_{GS} = \pm 20$ V | - | - | ± 100 | nA |
| | | $V_{GS} = 0 V$ | V _{DS} = - 30 V | - | - | - 1 | |
| Zero gate voltage drain current | I _{DSS} | $V_{GS} = 0 V$ | $V_{DS} = -30 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$ | - | - | - 50 | μA |
| | | $V_{GS} = 0 V$ | $V_{DS} = -30 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$ | - | - | - 150 | |
| On-state drain current ^a | I _{D(on)} | V _{GS} = - 10 V | V _{DS} = - 5 V | - 30 | - | - | Α |
| | | $V_{GS} = -10 V$ | I _D = - 7.5 A | - | 0.014 | 0.017 | |
| Ducin actures on state registeres a | P | $V_{GS} = -10 V$ | I _D = - 7.5A, T _J = 125 °C | - | - | 0.034 | Ω |
| Drain-source on-state resistance ^a | R _{DS(on)} | $V_{GS} = -10 V$ | I _D = - 7.5 A, T _J = 175 °C | - | - | 0.039 | |
| | | V _{GS} = - 4.5 V | I _D = - 5 A | - | 0.030 | 0.036 | |
| Forward transconductance b | g _{fs} | V _{DS} = | - 15 V, I _D = - 7.5 A | - | 18 | - | S |
| Dynamic ^b | • | | | | | | |
| Input capacitance | C _{iss} | | | - | 1345 | 1680 | |
| Output capacitance | C _{oss} | $V_{GS} = 0 V$ | V _{DS} = - 10 V, f = 1 MHz | - | 330 | 415 | pF |
| Reverse transfer capacitance | C _{rss} | | | - | 245 | 305 | |
| Total gate charge ^c | Qg | | | - | 33 | 50 | |
| Gate-source charge ^c | Q _{gs} | V _{GS} = - 10 V | $V_{DS} = -15 \text{ V}, \text{ I}_{D} = -9 \text{ A}$ | - | 5.5 | - | nC |
| Gate-drain charge ^c | Q _{gd} | | | - | 9.4 | - | |
| Gate resistance | Rg | | f = 1 MHz | 3 | 6.31 | 10.5 | Ω |
| Turn-on delay time ^c | t _{d(on)} | | | - | 12 | 18 | |
| Rise time ^c | t _r | | - 15 V, R _I = 1.66 Ω | - | 12 | 18 | |
| Turn-off delay time ^c | t _{d(off)} | I _D ≅ - 9 A, ' | $V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 6 \Omega$ | - | 39 | 59 | ns |
| Fall time ^c | t _f | 1 | | - | 28 | 42 | |
| Source-Drain Diode Ratings and Char | acteristics ^b | • | | | • | | |
| Pulsed current ^a | I _{SM} | | | - | - | - 120 | Α |
| Forward voltage | V _{SD} | le = | - 4.5 A, V _{GS} = 0 | - | - 0.8 | - 1.2 | V |

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

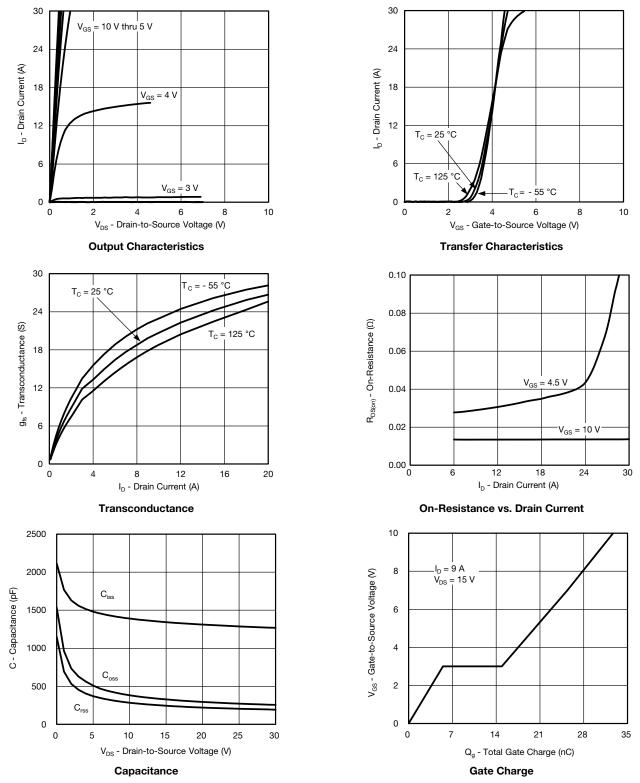
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



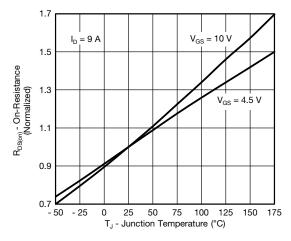
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

3

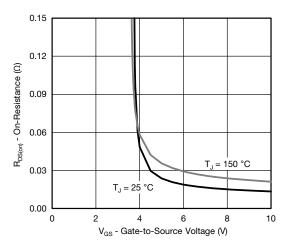


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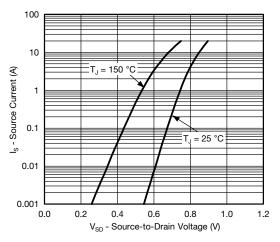
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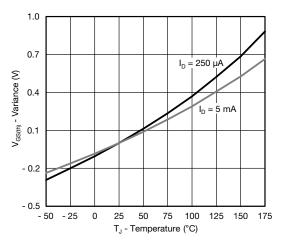
On-Resistance vs. Junction Temperature



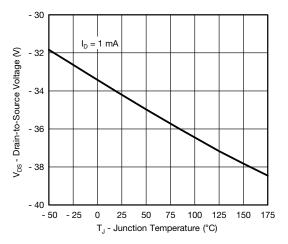
On-Resistance vs. Gate-to-Source Voltage



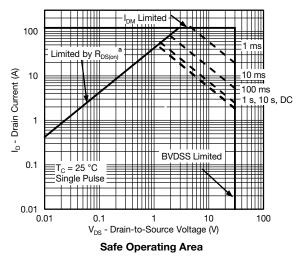
Source Drain Diode Forward Voltage



Threshold Voltage



BVDSS vs. Junction Temperature





a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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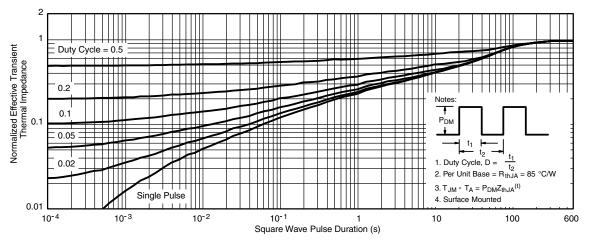


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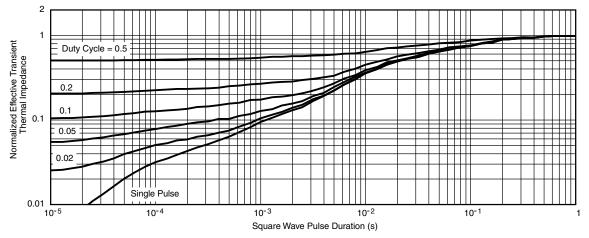
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

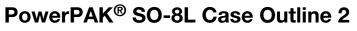


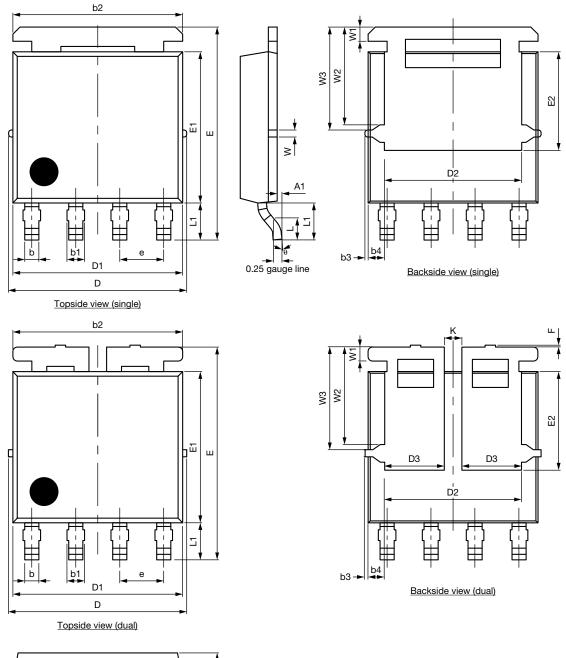
Normalized Thermal Transient Impedance, Junction-to-Case

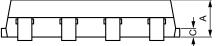
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Package Information



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| DIM. | MILLIMETERS | | | INCHES | | | |
|------|-------------|----------|-------|-----------|-----------|-------|--|
| | MIN. | NOM. | MAX. | MIN. | MIN. NOM. | | |
| А | 1.00 | 1.07 | 1.14 | 0.039 | 0.042 | 0.045 | |
| A1 | 0.00 | - | 0.127 | 0.00 | - | 0.005 | |
| b | 0.33 | 0.41 | 0.48 | 0.013 | 0.016 | 0.019 | |
| b1 | 0.44 | 0.51 | 0.58 | 0.017 | 0.020 | 0.023 | |
| b2 | 4.80 | 4.90 | 5.00 | 0.189 | 0.193 | 0.197 | |
| b3 | | 0.094 | | | 0.004 | | |
| b4 | | 0.47 | | | 0.019 | | |
| С | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 | |
| D | 5.00 | 5.13 | 5.25 | 0.197 | 0.202 | 0.207 | |
| D1 | 4.80 | 4.90 | 5.00 | 0.189 | 0.193 | 0.197 | |
| D2 | 3.86 | 3.96 | 4.06 | 0.152 | 0.156 | 0.160 | |
| D3 | 1.63 | 1.73 | 1.83 | 0.064 | 0.068 | 0.072 | |
| е | | 1.27 BSC | | 0.050 BSC | | | |
| E | 6.05 | 6.15 | 6.25 | 0.238 | 0.242 | 0.246 | |
| E1 | 4.27 | 4.37 | 4.47 | 0.168 | 0.172 | 0.176 | |
| E2 | 2.75 | 2.85 | 2.95 | 0.108 | 0.112 | 0.116 | |
| F | - | - | 0.15 | - | - | 0.006 | |
| L | 0.62 | 0.72 | 0.82 | 0.024 | 0.028 | 0.032 | |
| L1 | 0.92 | 1.07 | 1.22 | 0.036 | 0.042 | 0.048 | |
| К | | 0.51 | | | 0.020 | | |
| W | | 0.23 | | | 0.009 | | |
| W1 | 0.41 | | | 0.016 | | | |
| W2 | 2.82 | | | 0.111 | | | |
| W3 | | 2.96 | | | 0.117 | | |
| θ | 0° | - | 10° | 0° | - | 10° | |

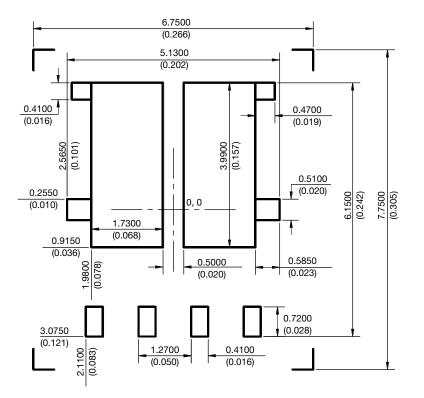
Note

• Millimeters will govern



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RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



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